

ABSTRACT

A method for forming a metal-insulator-metal (“MIM”) capacitor is provided. In the method, a first metal film and an dielectric film are sequentially formed on a semiconductor substrate. A trench through which the first metal film is exposed is formed by patterning the dielectric film. A insulation film and a second metal film are sequentially formed on a surface of the trench and the dielectric film. A mask pattern defining a capacitor forming area is provided on the second metal film. The second metal film and the insulation film are etched by using the mask pattern and the dielectric film as an etching barrier and an etching stopper layer, respectively, to form an upper electrode. With the mask pattern removed, a lower electrode is formed by patterning the dielectric film and the first metal film.